



### Product Description

GRF2013 is a broadband gain block with low noise figure and high linearity designed for small cell, wireless infrastructure and other high performance applications. It exhibits outstanding broadband NF, linearity and return losses over 0.7 to 3.8 GHz with a single match.

Optimizing the bias inductor and coupling caps for lower frequency operation will yield strong performance down to 50 MHz. For applications above 4 GHz, the addition of simple external matching yields outstanding linearity and gain performance up to 8 GHz.

The device is operated from a supply voltage of 2.7 to 8.0V with a selectable I<sub>ddq</sub> range of 15 to 100 mA for optimal efficiency and linearity.

Consult with the GRF applications engineering team for custom tuning/evaluation board data. De-embedded s-parameters are available on the website landing page for the device.

### Features

Reference: 5V/90mA/1.9 GHz

- Gain: 18.5 dB
- OIP3: 38.5 dBm
- OP1dB: 22.5 dBm
- NF: 1.3 dB

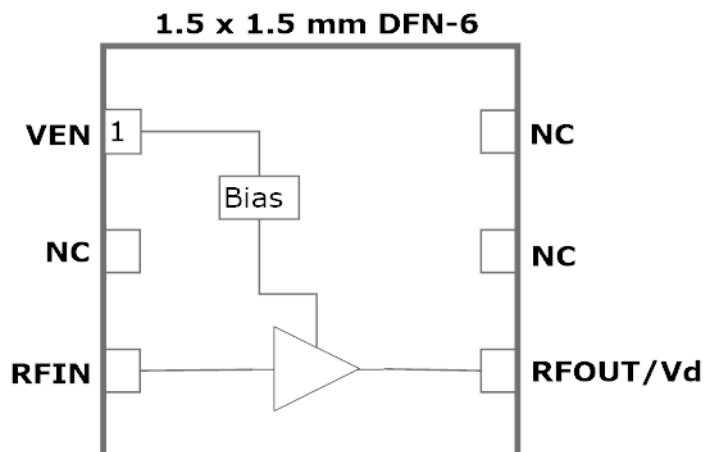
Reference: 8V/100mA/1.9 GHz

- Gain: 18.5 dB
- OIP3: 41.0 dBm
- OP1dB: 25.3 dBm
- NF: 1.4 dB

- Low Noise Figure
- Flat Gain
- Flexible Biasing
- Internally Matched to 50 Ω
- Process: GaAs pHEMT

### Applications

- Linear Driver Amplifier
- Small Cells and Cellular Repeaters
- IF Amplifier
- Wireless Backhaul



## Absolute Ratings:

Parameter	Symbol	Min.	Max.	Unit
Supply Voltage	V <sub>DD</sub>	0	9.0	V
RF Input Power: (Load VSWR < 2:1; V <sub>D</sub> : <= 8.0 volts)	P <sub>IN MAX</sub>		22	dBm
Operating Temperature (Package Heat Sink)	T <sub>AMB</sub>	-40	105	°C
Maximum Channel Temperature (MTTF > 10 <sup>6</sup> Hours)	T <sub>MAX</sub>		170	°C
Maximum Dissipated Power	P <sub>DISS MAX</sub>		1.0	W
<b>Electrostatic Discharge:</b>				
Charged Device Model:	CDM	1500		V
Human Body Model:	HBM	250		V
<b>Storage:</b>				
Storage Temperature	T <sub>STG</sub>	-65	150	°C
Moisture Sensitivity Level	MSL		1	--



**Caution!** ESD Sensitive Device

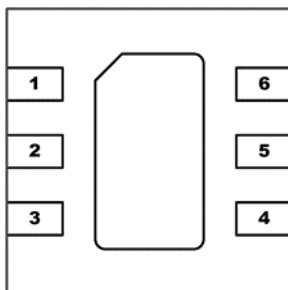


Exceeding Absolute Maximum Rating conditions may cause permanent damage to the device.

**Note:** For manufacturing information, see the [Guerrilla-RF.com](http://Guerrilla-RF.com) website for the following document located on the GRF2013 landing page: Manufacturing Note—MN-001 Product Tape and Reel, Solderability and Package Outline Specification:

[Link to manufacturing note](#)

### Pin Out (Top View)



### Pin Assignments:

Pin	Name	Description	Note
1	<b>V<sub>ENABLE</sub></b>	Enable Voltage Input	V <sub>ENABLE</sub> and series resistor set I <sub>DDQ</sub> . V <sub>ENABLE</sub> < 0.2 volts disables device. On-die pull-down resistor will turn the part off if this node is allowed to float.
2	<b>NC</b>	No Connect or Ground	No internal connection to die
3	<b>RF_In</b>	LNA RF input	Internally matched 50Ω. An external DC blocking cap must be used.
4	<b>RF_Out</b>	LNA RF output	Internally matched 50Ω. V <sub>DD</sub> must be applied through a choke to this pin
5	<b>NC</b>	No Connect or Ground	No internal connection to die
6	<b>NC</b>	No Connect or Ground	No internal connection to die
<b>PKG BASE</b>	<b>GND</b>	Ground	Provides DC and RF ground for LNA, as well as thermal heat sink. Recommend multiple 8 mil vias beneath the package for optimal RF and thermal performance. Refer to evaluation board top layer graphic on schematic page.



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# GRF2013

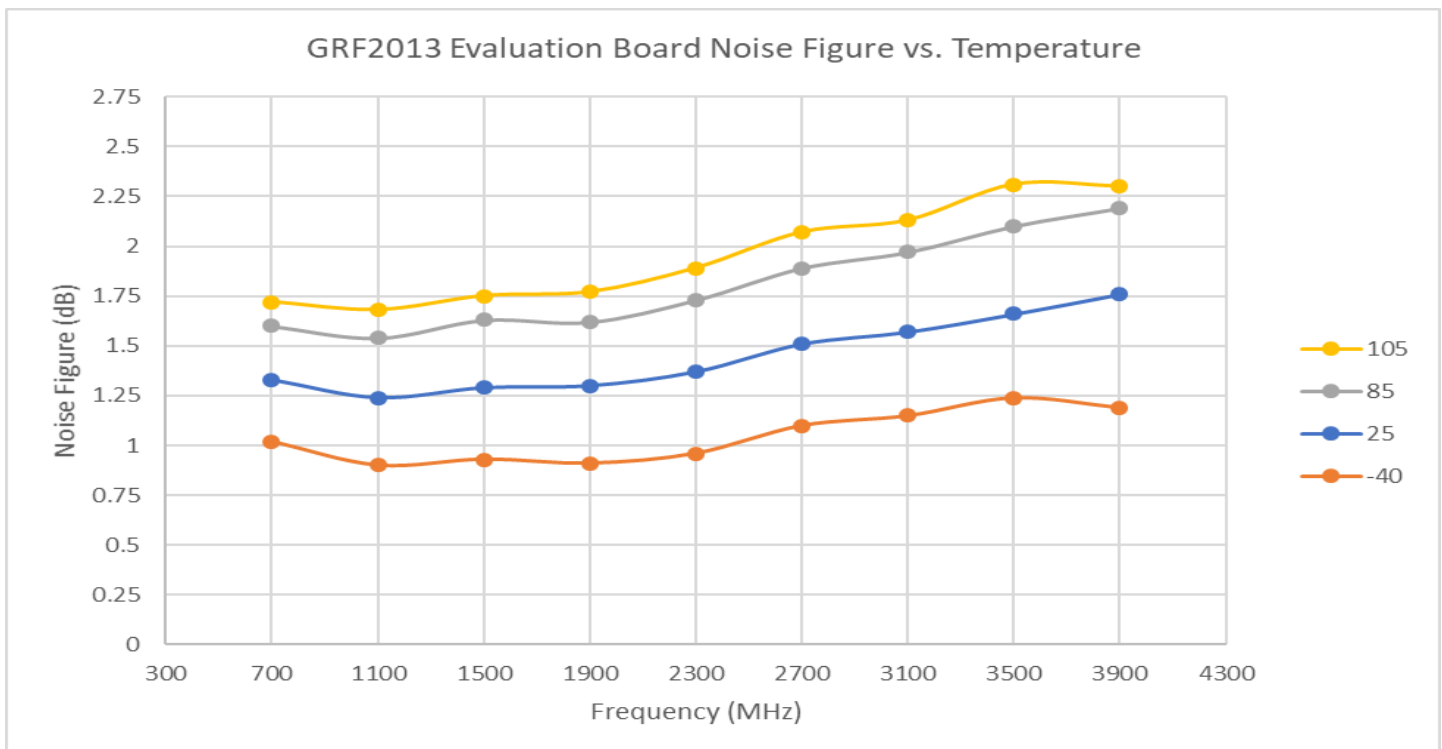
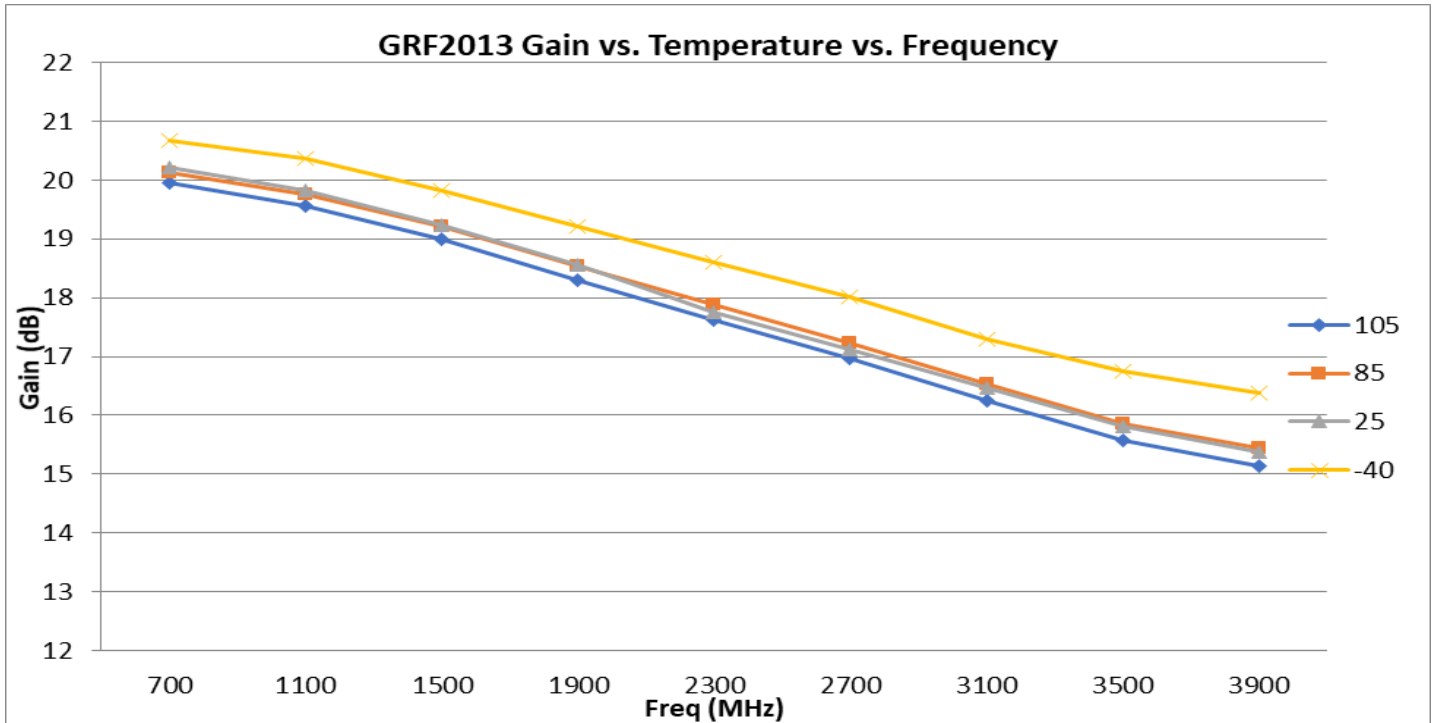
**Broadband Linear Gain Block**  
**0.05 to 8.0 GHz**

## Nominal Operating Parameters:

Parameter	Symbol	Specification			Unit	Condition
		Min.	Typ.	Max.		
Test Frequency	$F_{TEST}$		1.9		GHz	$V_{DD} = 5.0\text{ V}$ , $T_A = 25^\circ\text{C}$
Gain	S21	17.5	18.5		dB	
Evaluation Board Noise Figure	NF		1.3	1.5	dB	
Output 3rd Order Intercept	OIP3		38.5		dBm	4.0 dBm $P_{OUT}$ per tone (1899 and 1901 MHz)
Output 1dB Compression Power	OP1dB	21.0	22.5		dBm	
Switching Rise Time	$T_{RISE}$		500		ns	
Switching Fall Time	$T_{FALL}$		500		ns	
Supply Current	$I_{DD}$		90.0		mA	
Enable Current	$I_{ENABLE}$		5.0		mA	
<b>Disabled Mode</b>						
Leakage Current	$I_{LEAKAGE}$		100		$\mu\text{A}$	$V_{DD} = 5.0\text{V}$ ; $V_{ENABLE} = 0.0\text{V}$
<b>Thermal Data</b>						
Thermal Resistance: (Infra-Red Scan)	$\theta_{JC}$		52		$^\circ\text{C/W}$	On standard Evaluation Board
Channel Temperature @ +85 C Reference (Package heat sink)	$T_{CHANNEL}$		109 (See note)		$^\circ\text{C}$	$V_{DD} = 5.0\text{ V}$ ; $I_{DDQ} = 90\text{ mA}$ ; No RF; $P_{DISS} = 450\text{ mW}$

Note: MTTF >10<sup>6</sup> hours for  $T_{CHANNEL} < 170$  degrees C.

## GRF2013 Evaluation Board Measured Data: (0.7 to 3.8 GHz Tune)



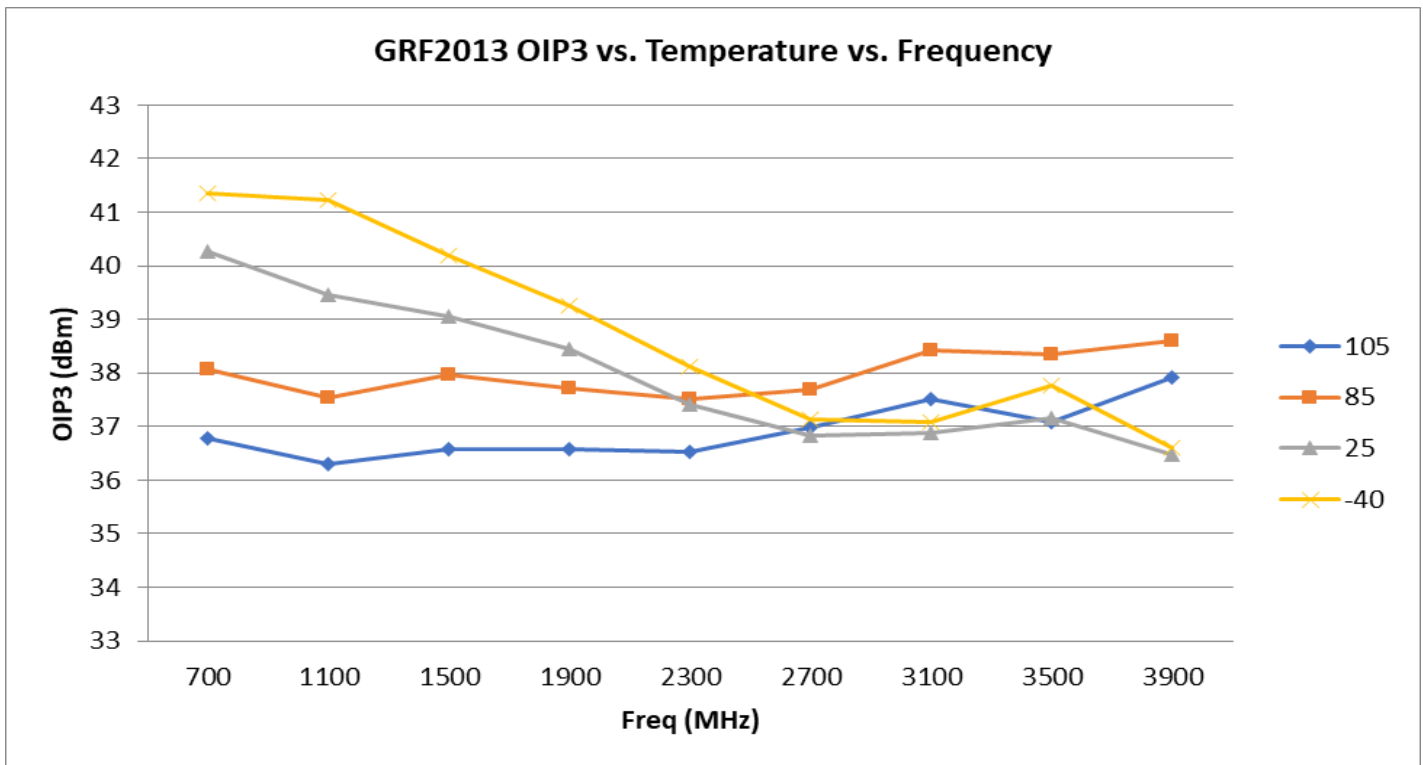
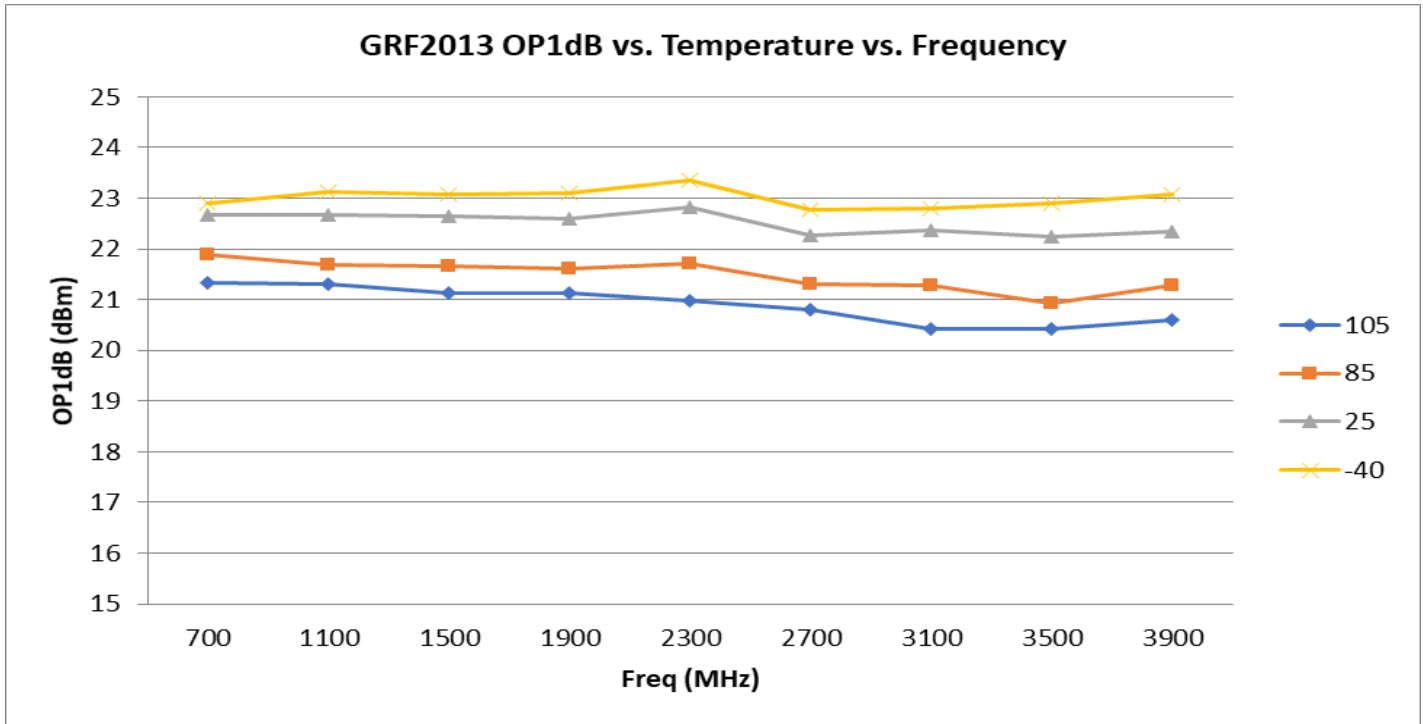


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Broadband Linear Gain Block  
0.05 to 8.0 GHz

## GRF2013 Evaluation Board Data: (0.7 to 3.8 GHz Tune)



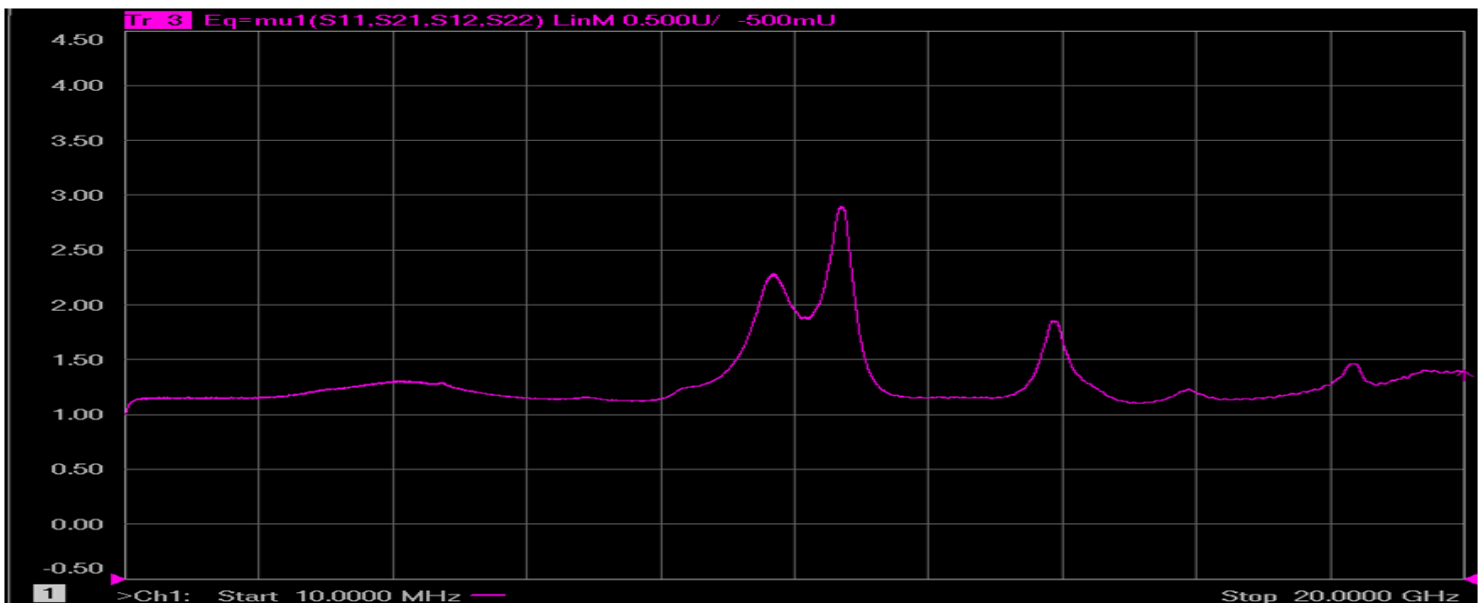
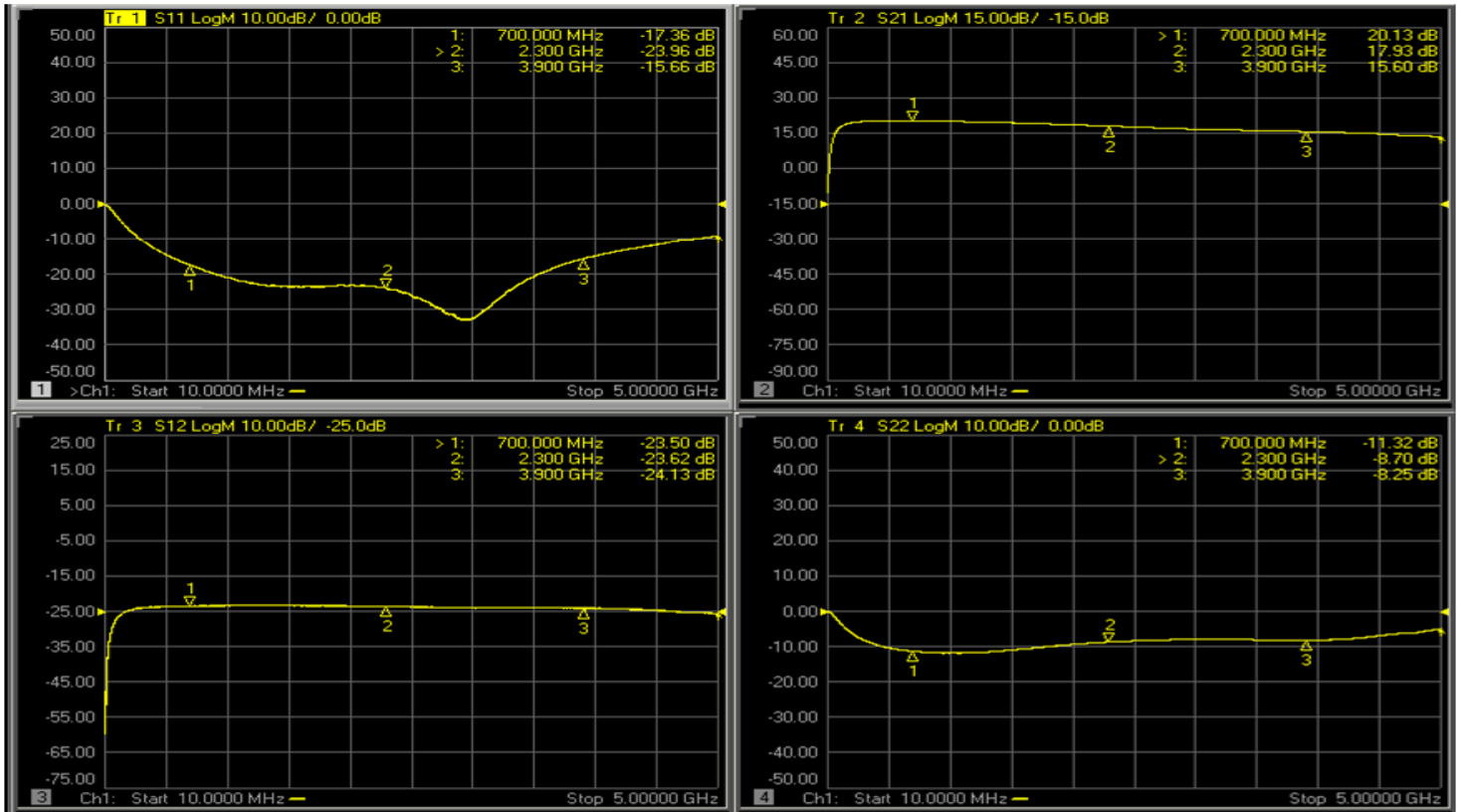


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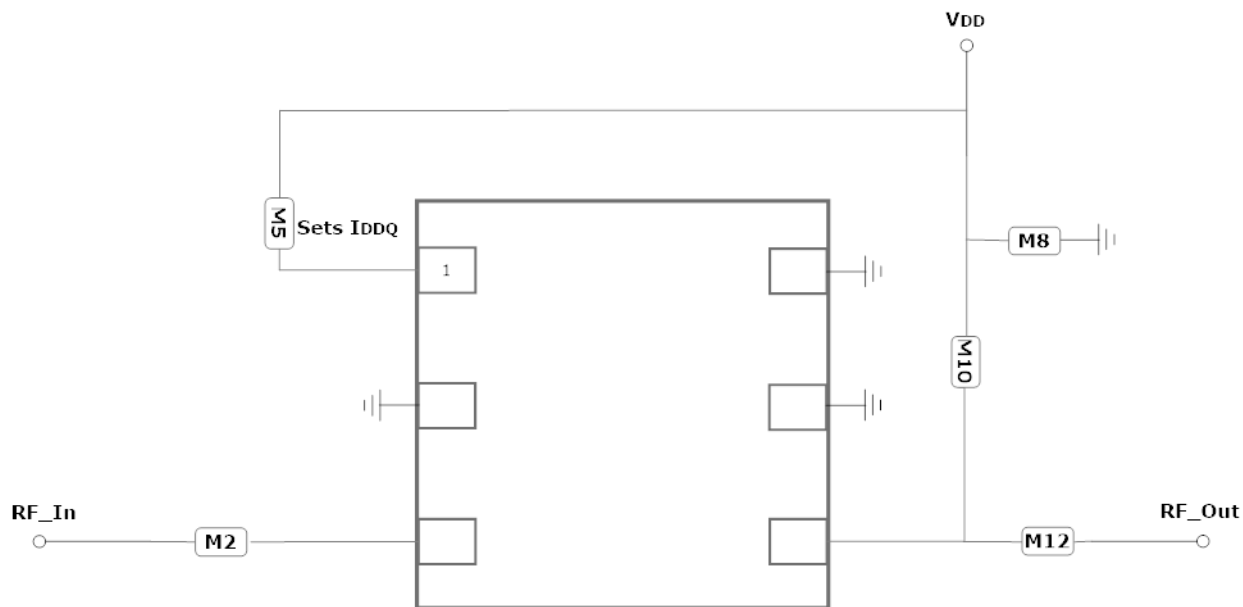
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0.05 to 8.0 GHz

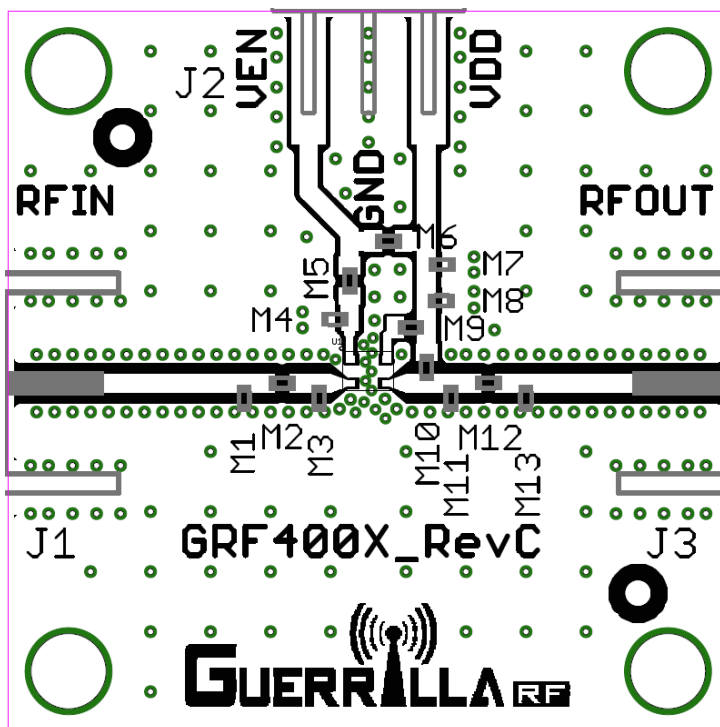
## GRF2013 Evaluation Board S-Pars and Stability Mu Factor: (0.7 to 3.8 GHz Tune)



Note: Mu factor  $\geq 1.0$  implies unconditional stability.



GRF2013 Application Schematic



GRF2013 Evaluation Board Assembly Diagram





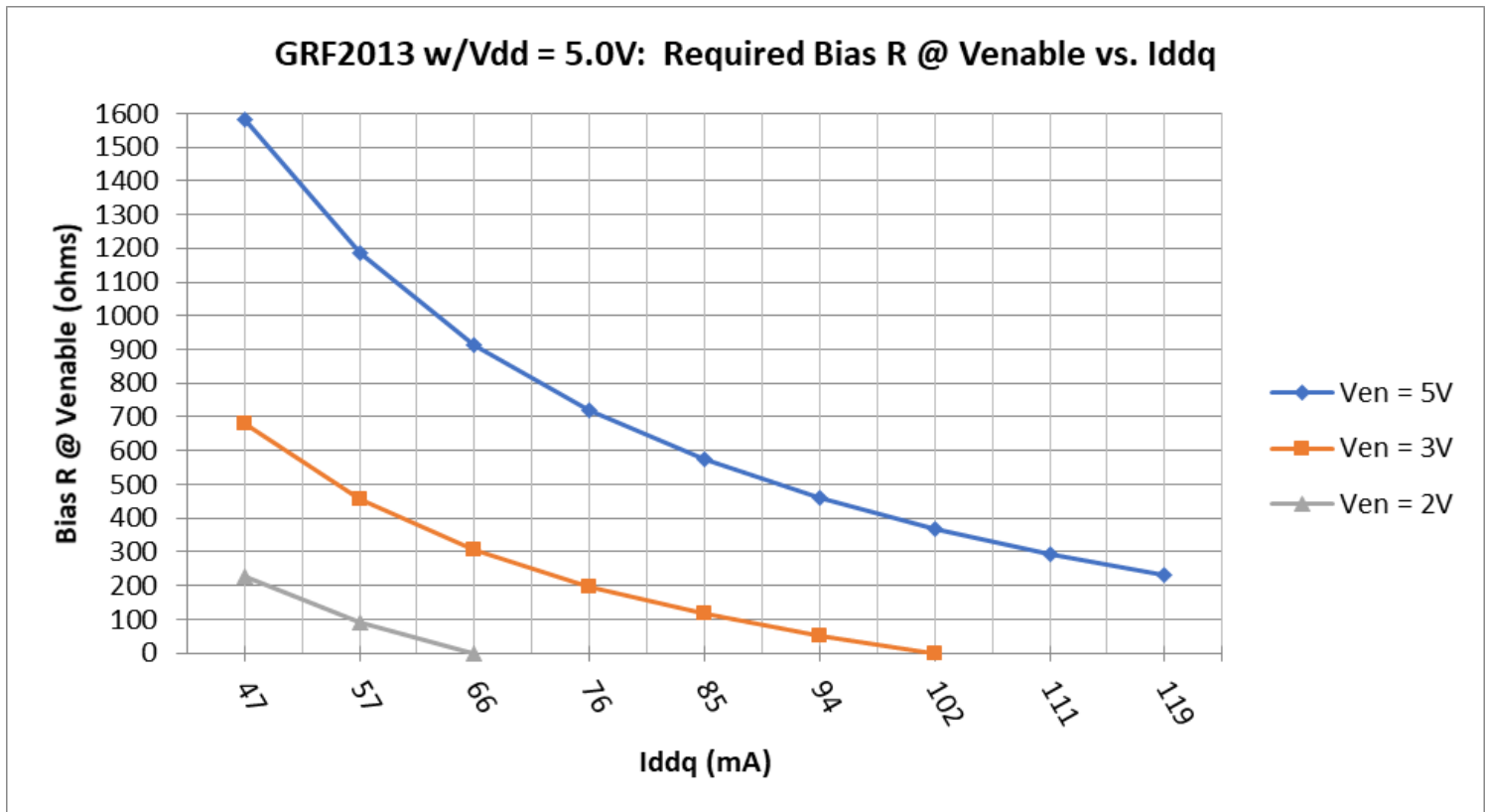
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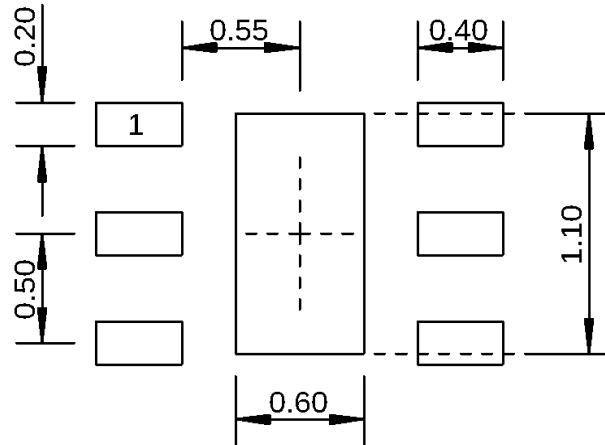
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Broadband Linear Gain Block  
0.05 to 8.0 GHz

## GRF2013 Standard Evaluation Board BOM: (0.7 to 3.8 GHz Tune)

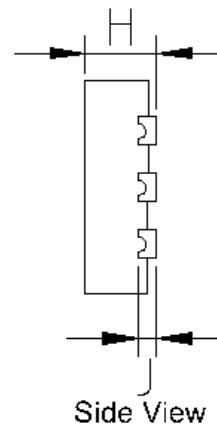
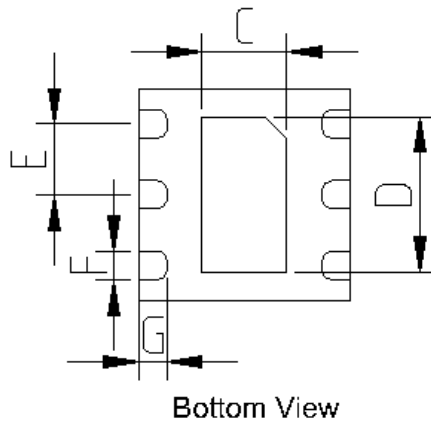
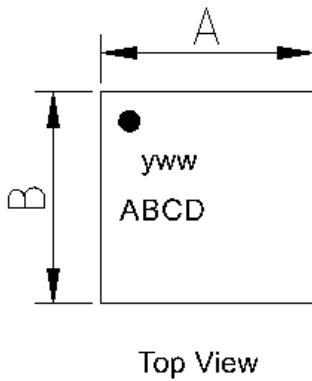
Component	Type	Manufacturer	Family	Value	Package Size	Substitution
M2	Capacitor	Murata	GRM	100 pF	0402	ok
M5 (See curves)	Resistor	Various	5%	Sets Iddq	0402	ok
M8	Capacitor	Murata	GRM	0.1 uF	0402	ok
M10	Inductor	Various	MLC	33 nH	0402	ok
M12	Capacitor	Murata	GRM	100 pF	0402	ok
Evaluation Board	GRF400X_RevC					





Dimensions in millimeters

### 1.5 mm DFN-6 Suggested PCB Footprint (Top View)



Dimensions (MM)	
A	1.5 +/- 0.050
B	1.5 +/- 0.050
C	.6 +/- 0.050
D	1.1 +/- 0.050
E	.5 Bsc
F	.2 +/- 0.050
G	.2 +/- 0.050
H	.45 +/- 0.050
J	.12 Ref.

### 1.5 mm DFN-6 Package Dimensions



Released

# GRF2013

## Broadband Linear Gain Block 0.05 to 8.0 GHz

Data Sheet Release Status:	Notes
Advance	S-parameter and NF data based on EM simulations for the fully packaged device using foundry supplied transistor s-parameters. Linearity estimates based on device size, bias condition and experience with related devices.
Preliminary	All data based on evaluation board measurements in the Guerrilla RF Applications Lab.
Released	All data based on device qualification data. Typically, this data is nearly identical to the data found in the preliminary version. Max and min values for key RF parameters are included.

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